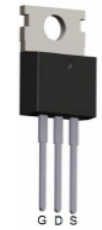
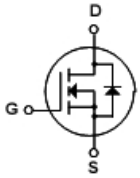
TS85N08

80A 85V N-Channel Enhancement Mode Power Mosfet

DRAWING





Features

- 80A,85V,R_{DSON}=8.5mΩ@V_{GS}=10V
- Special process technology for high ESD capability
- High density cell design for ultra low Rdson
- Fully characterized Avalanche voltage and current
- Good stability and uniformity with high Eas
- Excellent package for good heart dissipation

General Description

- Package:TO-220C
- The TS85N08 uses advanced trench technology and design to provide excellent T_{dson} with low gate charge. It can be used in a wide variety of applications.

Absolute Maximum Ratings(Tc=25℃ unless otherwise noted)

Symbol	Parameter	Spec	Units
V_{DSS}	Drain-Source Voltage	85	V
I_D	Drain Current -Continuous(Tc=25℃)	80	A
I_D	Drain Current -Continuous(Tc=100℃)	60	A
I_{DM}	Drain Current -Pulsed	320	A
V_{GSS}	Gate-Source Voltage	±20	V
P_D	Maximum Power Dissipation	170	W
	Derating factor	1.13	w/℃
dv/dt	Peak diode recovery voltage	15	V/ns
E_{AS}	Single Pulsed Avalanche Energy (Note 5)	620	mJ
T_J.T_{STG}	Operating Junction and Storage Temperature Range	-55 to +175	℃
R_{JC}	Thermal Resistance, Junction-to-Casec (Note 2)	0.88	℃/W

Electrical Characteristics(TA=25℃ unless otherwise noted)

Off Characteristics

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V,I_D=250uA	87	89	_	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=85V,V_{GS}=0V	_	_	1	uA
I_{GSS}	Gate-Body Leakage Current,	V_{GS}=±20V,Vds=0V	_	_	±100	nA

On Characteristics (Note 3)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250uA	2.0	2.85	4.0	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V,I_D=40A	_	6.8	8.5	mΩ
g_{FS}	Forward Transconductance	V_{DS}=25V,I_D=40A	110	-	-	S

Dynamic Characteristics (Note 4)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Cjss	Input Capacitance	VDS=25V,	_	4400		PF
Coss	Output Capacitance	VGS=0V,	_	340		PF
Crss	Reverse Transfer Capacitance	f=1.0MHz	_	260		PF

Switching Characteristics (Note 4)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
t_{don}	Turn-On Delay Time	V_{DD}=30V,I_D=2A R_G=2.5Ω R_L=15Ω VGS=10V	_	18	_	ns
t_r	Turn-On Rise Time		_	12	_	ns
t_{doff}	Turn-Off Delay Time		_	56	_	ns
t_f	Turn-Off Fall Time		_	15	_	ns
Q_g	Total Gate Charge	V_{DS}=30V I_D=30A V_{GS}=10V	_	100	_	nc
Q_{gs}	Gate-Source Charge		_	20	_	nc
Q_{gd}	Gate-Drain Charge		_	30	_	nc

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Is	diode forward current (Note 3)		_	_	80	A
Vsd	diode forward Voltage (Note 2)	VGS=0V,IS=40A	_	_	1.2	V
Trr	Reverse Recovery Time	TJ=25℃,IF=75A dif/dt=100A/us (Note 3)	_	_	36	ns
Qrr	Reverse Recovery charge		_	_	56	uc
T_{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible(turn-on is dominated by LS+LD)				

Notes:

1.Repetitive Rating: Pulse width limited by maximum junction temperature.

2.Surface Mounted on FR4 Board, t≤10 sec

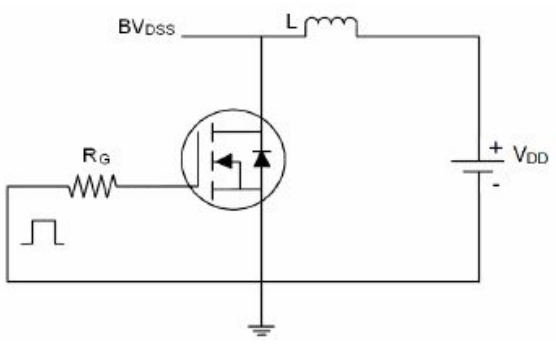
3.Pulse Test: Pulse Width ≤300us,Duty cycle≤2%

4.Guaranteed by design, not subject to production

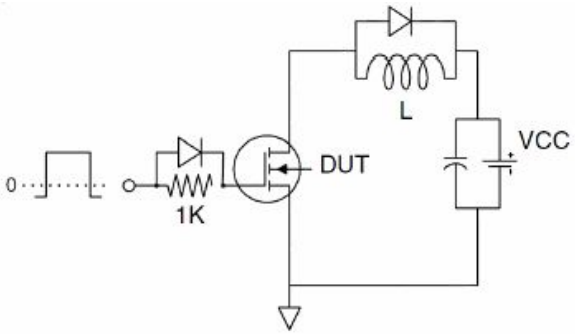
5.EAS condition: Tj=25℃,VDD=50V,VG=10V,L=2mH,Rg=25Ω

Test circuits

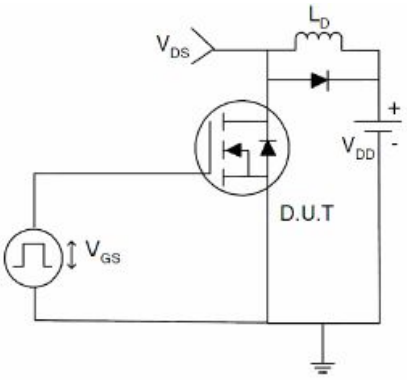
1)EAS Test Circuits



2)Cate Charge Test Circuit



3）Switch Time Test Circuit



Typical Electrical And Thermal Characteristics(Curves)

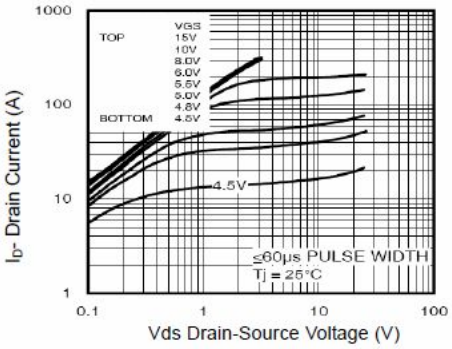


Figure 1 Output Characteristics

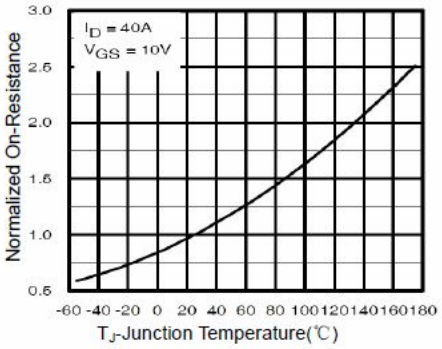


Figure 4 Rdson-JunctionTemperature

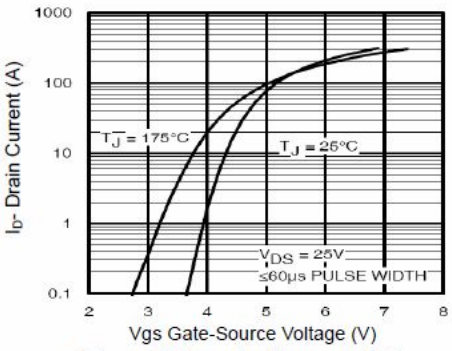


Figure 2 Transfer Characteristics

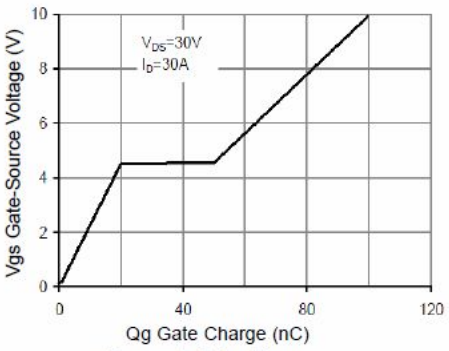


Figure 5 Gate Charge

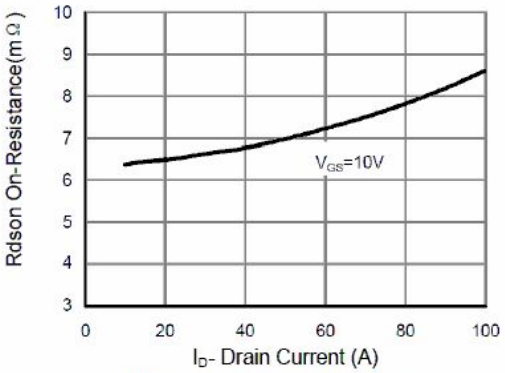


Figure 3 Rdson- Drain Current

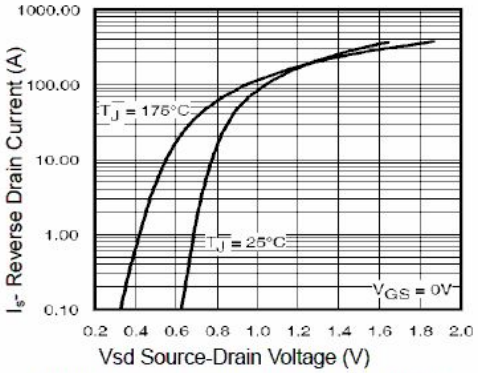


Figure 6 Source- Drain Diode Forward

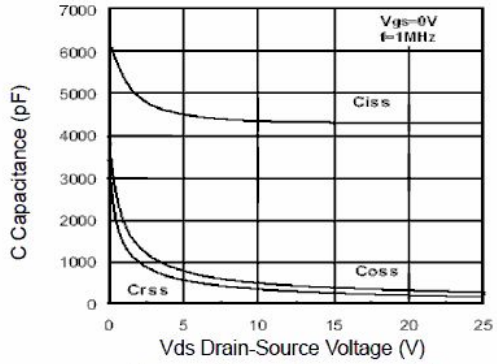


Figure 7 Capacitance vs Vds

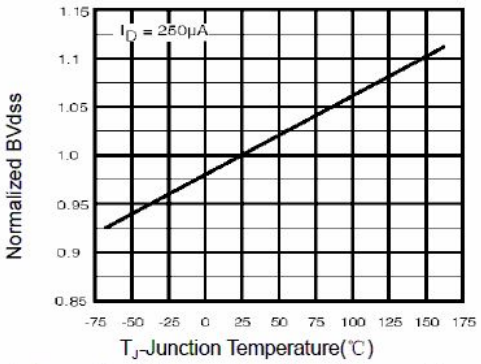


Figure 9 BV_{DSS} vs Junction Temperature

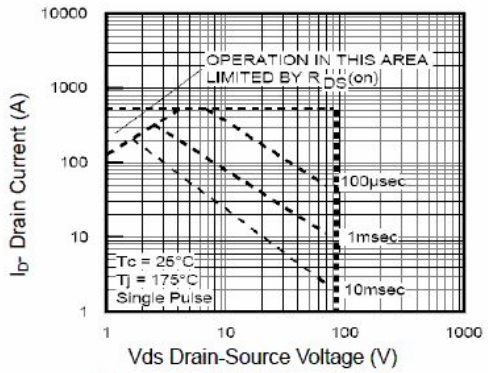


Figure 8 Safe Operation Area

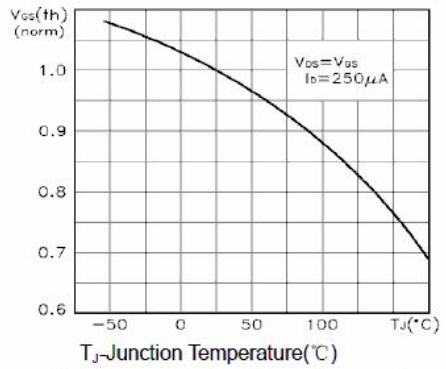


Figure 10 $V_{GS(th)}$ vs Junction Temperature

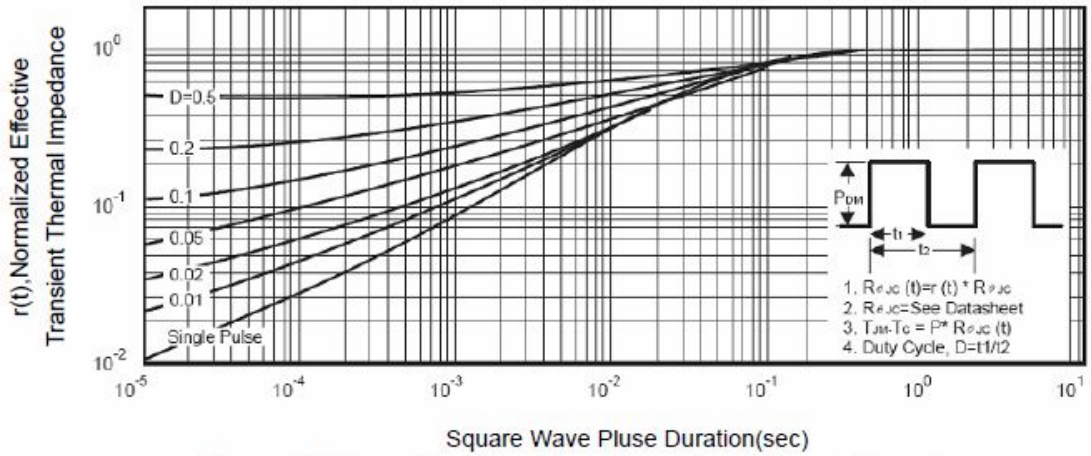


Figure 11 Normalized Maximum Transient Thermal Impedance

Mechanical Dimensions